

Plastic Silicon Infrared Phototransistor

QSD123, QSD124

Description

The QSD123/124 is a phototransistor encapsulated in an infrared transparent, black T-1 3/4 package.

Features

- PNPN Silicon Phototransistor
- Package Type: T €

QSD123, QSD124

ELECTRICAL CHARACTERISTICS (T_A = 25 C)

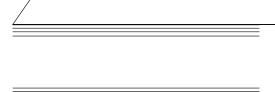
Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
PS	Peak Sensitivity Wavelength		_	880	-	nm
	Reception Angle		_	±12	-	-
I _{CEO}	Collector-Emitter Dark Current	V _{CE} = 10 V, Ee = 0	_	-	100	nA
BV _{CEO}	Collector-Emitter Breakdown	I _C = 1 mA	30	_	-	V
BV _{ECO}	Emitter-Collector Breakdown	I _E = 100 μA	5	-	-	V
I _{C(ON)}	On–State Collector Current (Note 5) QSD123 QSD124	Ee = 0.5 mW/cm^2 , $V_{CE} = 5 \text{ V}$	4 6	- -	16 29	mA
V _{CE(SAT)}	Saturation Voltage (Note 5)	Ee = 0.5 mW/cm ² , $I_C = 0.5$ mA	_	_	0.4	V
t _r	Rise Time	$V_{CC} = 5 \text{ V}, R_L = 100 \Omega, I_C = 0.2 \text{ mA}$	_	7	-	μs
t _f	Fall Time	1	_	7	-	μs

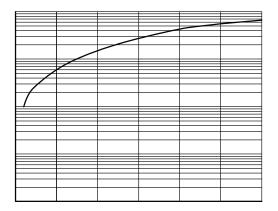
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

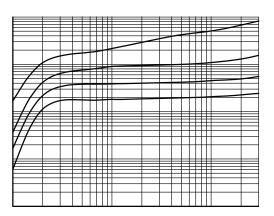
5. $\lambda = 880$ nm, AlGaAs.

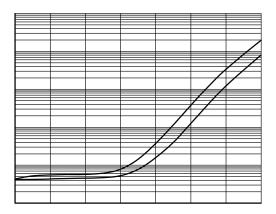
QSD123, QSD124

TYPICAL PERFORMANCE CHARACTERISTICS







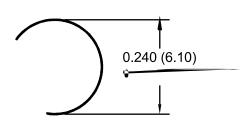


T-1 3/4, 5MM DETECTOR CASE 100CE ISSUE O

DATE 30 NOV 2016

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